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June 2014

FDB024N08BL7

N-Channel PowerTrench[®] MOSFET 80 V, 229 A, 2.4 m Ω

Features

- $R_{DS(on)}$ = 1.7 m Ω (Typ.) @ V_{GS} = 10 V, I_D = 100 A
- Low FOM R_{DS(on)} *Q_G
- Low Reverse Recovery Charge, Q_{rr} = 112 nC
- · Soft Reverse Recovery Body Diode
- · Enables Highly Efficiency in Synchronous Rectification
- · Fast Switching Speed
- · RoHS Compliant
- Qualified according to JEDEC Standards JESD22-A113F and IPC/JEDEC J-STD-020D.1

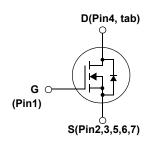
Description

This N-Channel MOSFET is produced using Fairchild Semiconductor's advance PowerTrench® process that has been tailored to minimize the on-state resistance while maintaining superior switching performance.

Applications

- Synchronous Rectification for ATX / Server / Telecom PSU
- · Battery Protection Circuit
- · Motor drives and Uninterruptible Power Supplies





MOSFET Maximum Ratings T_C = 25°C unless otherwise noted

1. Gate
2. Source
3. Source
4. Drain
5. Source
6. Source
7. Source

Symbol		Parameter	FDB024N08BL7	Unit
V _{DSS}	Drain to Source Voltage		80	V
V _{GSS}	Gate to Source Voltage		±20	V
		- Continuous (T _C = 25°C, Silicon Limited)	229*	
I _D	Drain Current	- Continuous (T _C = 100°C, Silicon Limited)	162*	Α
		- Continuous (T _C = 25°C, Package Limited)	120	
I _{DM}	Drain Current	- Pulsed (Note 1)	916	Α
E _{AS}	Single Pulsed Avalanche Er	Single Pulsed Avalanche Energy (Note 2)		
dv/dt	Peak Diode Recovery dv/dt	(Note 3)	6.0	V/ns
D	Dower Discipation	$(T_C = 25^{\circ}C)$	246	W
P_{D}	Power Dissipation	- Derate Above 25°C	1.64	W/°C
T _J , T _{STG}	Operating and Storage Tem	-55 to +175	°C	
T _L	Maximum Lead Temperature 1/8" from Case for 5 Second	300	°C	

^{*}Calculated continuous current based on maximum allowable junction temperature. Package limitation current is 120 A.

Thermal Characteristics

Symbol	Parameter FDB024N		Unit
$R_{\theta JC}$	Thermal Resistance, Junction to Case, Max.	0.61	°C/W
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient, Max.	62.5	30/00

Package Marking and Ordering Information

Part Number	Top Mark	Package	Packing Method	Reel Size	Tape Width	Quantity
FDB024N08BL7	FDB024N08B	D2PAK-7L	Tape and Reel	330 mm	24 mm	800 units

Electrical Characteristics $T_C = 25^{\circ}C$ unless otherwise noted

Symbol	Parameter	Test Conditions	Min.	Тур.	Max.	Unit
Off Charac	cteristics					
BV _{DSS}	Drain to Source Breakdown Voltage	I _D = 250 μA, V _{GS} = 0 V	80	-	-	V
$\frac{\Delta BV_{DSS}}{\Delta T_{J}}$	Breakdown Voltage Temperature Coefficient	I_D = 250 μA, Referenced to 25°C	-	0.05	-	V/°C
I	Zero Gate Voltage Drain Current	V _{DS} = 64 V, V _{GS} = 0 V	-	-	1	μА
IDSS	Zero Gate Voltage Drain Current	$V_{DS} = 64 \text{ V}, T_{C} = 150^{\circ}\text{C}$	-	-	500	μΑ
I _{GSS}	Gate to Body Leakage Current	V _{GS} = ±20 V, V _{DS} = 0 V	-	-	±100	nA

On Characteristics

V _{GS(th)}	Gate Threshold Voltage	$V_{GS} = V_{DS}, I_{D} = 250 \mu A$	2.5	-	4.5	V
R _{DS(on)}	Static Drain to Source On Resistance	V _{GS} = 10 V, I _D = 100 A	-	1.7	2.4	mΩ
g _{FS}	Forward Transconductance	V _{DS} = 10 V, I _D = 100 A	-	227	-	S

Dynamic Characteristics

C _{iss}	Input Capacitance	V 40.V V 0.V	-	10170	13530	pF
C _{oss}	Output Capacitance	$V_{DS} = 40 \text{ V}, V_{GS} = 0 \text{ V},$ f = 1 MHz	-	1670	2220	pF
C _{rss}	Reverse Transfer Capacitance	I = I IVIDZ		35	-	pF
C _{oss} (er)	Engry Related Output Capacitance	V _{DS} = 40 V, V _{GS} = 0 V	-	3025	-	pF
Q _{g(tot)}	Total Gate Charge at 10V		-	137	178	nC
Q _{gs}	Gate to Source Gate Charge $V_{DS} = 40 \text{ V}, V_{GS} = 10 \text{ V},$		-	56	-	nC
Q _{gs2}	Gate Charge Threshold to Plateau	I _D = 100 A	-	25	-	nC
Q_{gd}	Gate to Drain "Miller" Charge	(Note 4)	-	28	-	nC
ESR	Equivalent Series Resistance (G-S)	f = 1MHz	-	2.4	-	Ω

Switching Characteristics

t _{d(on)}	Turn-On Delay Time		-	47	104	ns
t _r		$V_{DD} = 40 \text{ V}, I_{D} = 100 \text{ A},$	- /	66	142	ns
t _{d(off)}	Turn-Off Delay Time	$V_{GS} = 10 \text{ V}, R_{G} = 4.7 \Omega$	-	87	184	ns
t _f	Turn-Off Fall Time	(Note 4)	-	41	92	ns

Drain-Source Diode Characteristics

Is	Maximum Continuous Drain to Source Diode Forward Current			-	229*	Α
I _{SM}	Maximum Pulsed Drain to Source Diode Forward Current		-	-	916	Α
V_{SD}	Drain to Source Diode Forward Voltage	V _{GS} = 0 V, I _{SD} = 100 A	1	-	1.3	V
t _{rr}	Reverse Recovery Time	V _{GS} = 0 V, V _{DD} = 40 V, I _{SD} = 100 A,	-	80	-	ns
Q _{rr}	Reverse Recovery Charge	$dI_F/dt = 100 A/\mu s$	-	112	-	nC

Notes

- ${\it 1. Repetitive\ rating: pulse\ width\ limited\ by\ maximum\ junction\ temperature.}$
- 2. L = 3 mH, I $_{AS}$ = 24.72 A, R $_{G}$ = 25 Ω , starting T $_{J}$ = 25°C.
- 3. I $_{SD} \leq$ 100 A, di/dt \leq 200 A/µs, V $_{DD} \leq$ BV $_{DSS}$, starting T $_{J}$ = 25°C.
- 4. Essentially independent of operating temperature typical characteristics.

Typical Performance Characteristics

Figure 1. On-Region Characteristics

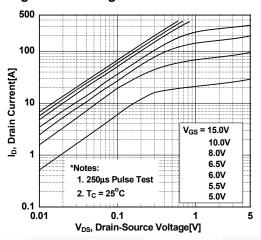


Figure 3. On-Resistance Variation vs.

Drain Current and Gate Voltage

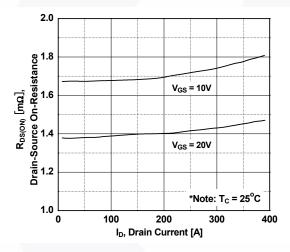


Figure 5. Capacitance Characteristics

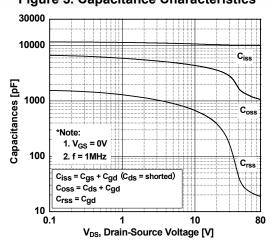


Figure 2. Transfer Characteristics

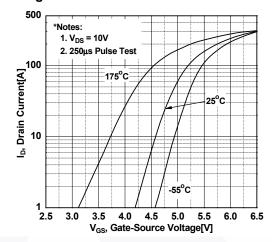


Figure 4. Body Diode Forward Voltage Variation vs. Source Current and Temperature

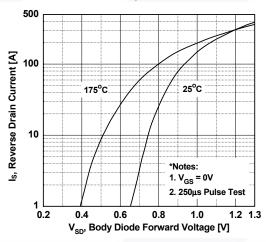
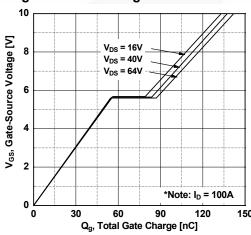


Figure 6. Gate Charge Characteristics



Typical Performance Characteristics (Continued)

Figure 7. Breakdown Voltage Variation vs. Temperature

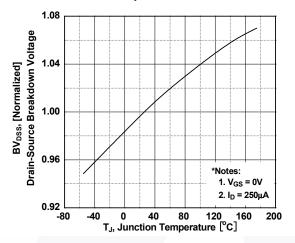


Figure 8. On-Resistance Variation vs. Temperature

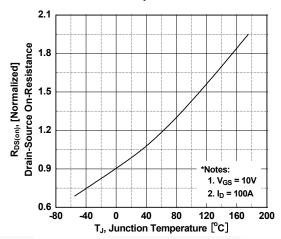


Figure 9. Maximum Safe Operating Area

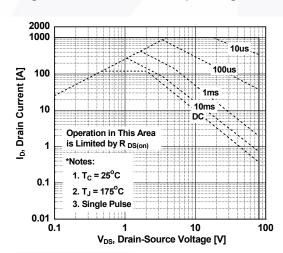


Figure 10. Maximum Drain Current vs. Case Temperature

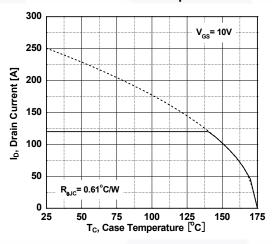


Figure 11. Eoss vs. Drain to Source Voltage

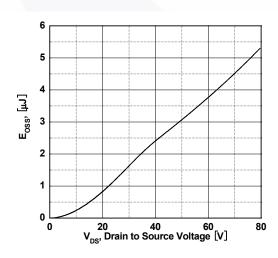
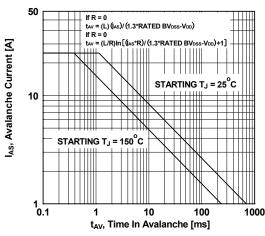


Figure 12. Unclamped Inductive Switching Capability



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Typical Performance Characteristics (Continued)

Figure 12. Transient Thermal Response Curve

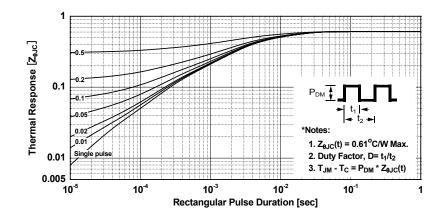


Figure 13. Gate Charge Test Circuit & Waveform

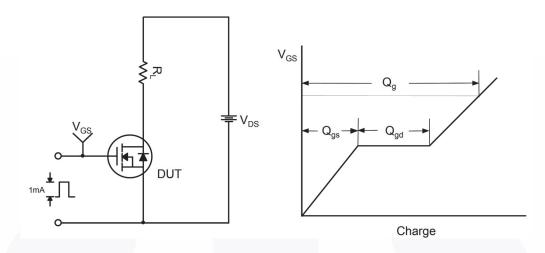


Figure 14. Resistive Switching Test Circuit & Waveforms

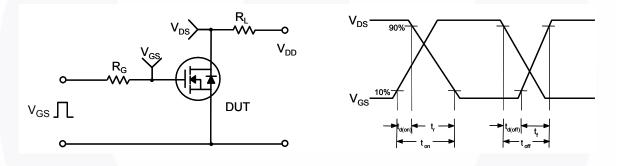
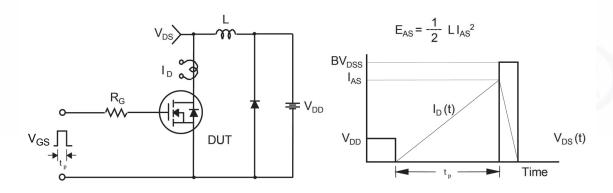
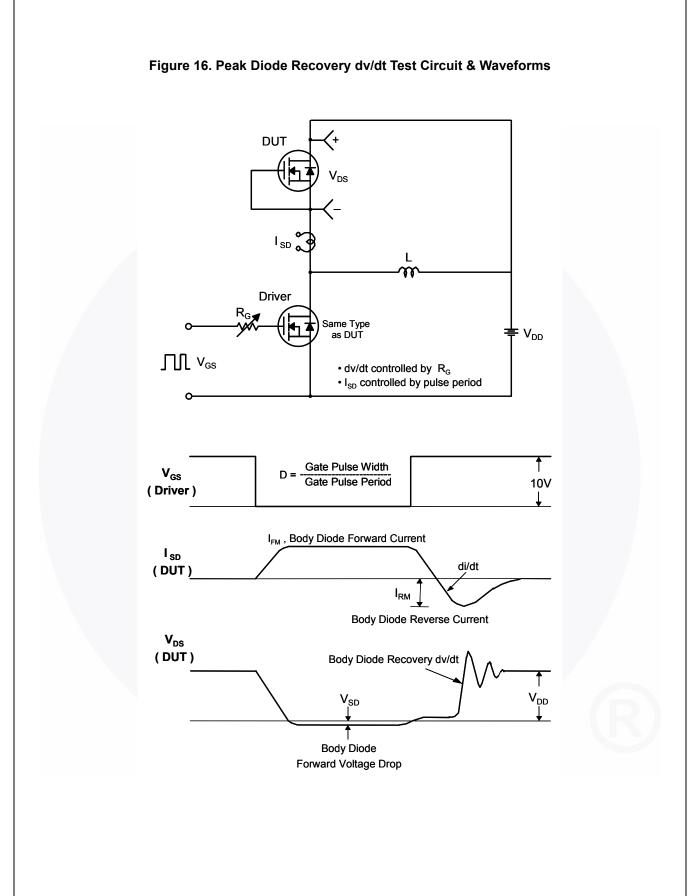


Figure 15. Unclamped Inductive Switching Test Circuit & Waveforms





Mechanical Dimensions

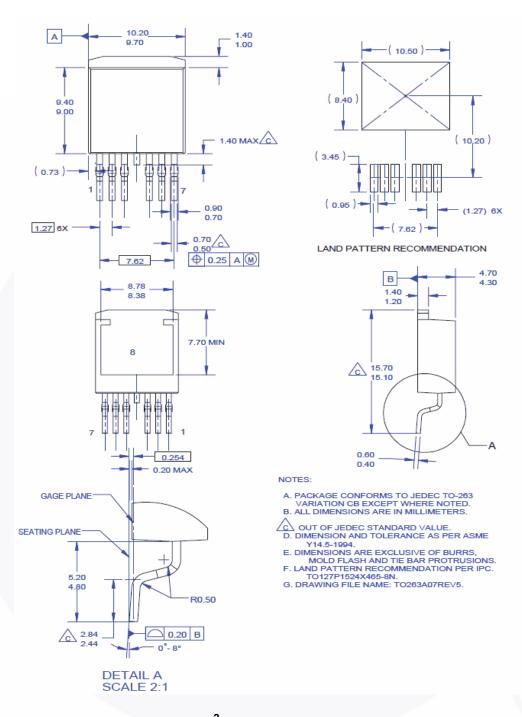


Figure 17. TO263 (D²PAK), Molded, 7-Lead, Surface Mount

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